

Form PTO-449

INFORMATION DISCLOSURE CITATION
IN AN APPLICATION

(Use several sheets if necessary)

Docket Number 356952001300

Application Number 10/774,011

Applicant

Guanghua WU et al.

Filing Date February 6, 2004

Group Art Unit 2856

Mailing Date May 14, 2004

U.S. PATENT DOCUMENTS

Examiner Initials	Ref. No.	Date	Document No.	Name	Class	Subclass	Filing Date If Appropriate
JC	1.	11/06/2003	2003/0205739	Yamada et al.			
	2.	09/22/1981	4,291,293	Bean			
	3.	09/22/1987	4,663,648	Yamada et al.			
	4.	03/1988	4,730,496	Knecht et al.			
	5.	10/1991	5,060,526	Barth et al.			
	6.	11/19/1991	5,065,978	Albarda et al.			
	7.	07/1992	5,132,658	Dauenhauer et al.			
	8.	09/1992	5,142,781	Mettner et al.			
	9.	01/12/93	5,179,499	MacDonald et al.			
	10.	03/30/93	5,198,390	MacDonald et al.			
	11.	08/10/93	5,235,187	Arney et al.			
	12.	08/1993	5,238,223	Mettner et al.			
	13.	02/1994	5,285,097	Hirai			
	14.	02/15/94	5,287,082	Arney et al.			
	15.	05/31/94	5,316,979	MacDonald et al.			
	16.	11/08/94	5,363,021	MacDonald			
	17.	12/20/94	5,375,033	MacDonald			
	18.	01/1995	5,386,142	Kurtz et al.			
	19.	02/28/95	5,393,375	MacDonald			
	20.	02/1995	5,393,711	Biallas et al.			
	21.	03/14/95	5,397,904	Arney et al.			
	22.	03/21/95	5,399,415	Chen et al.			
	23.	03/28/1995	5,400,824	Gschwendtner et al.			
	24.	06/20/95	5,426,070	Shaw et al.			
	25.	04/09/96	5,506,175	Zhang et al.			
	26.	07/16/96	5,536,988	Zhang et al.			

EXAMINER: John Chapman

DATE CONSIDERED: 6/26/05

EXAMINER: Initial if citation considered, whether or not the citation conforms with MPEP 609. Draw a line through the citation if not in conformance and not considered. Include a copy of this form with next communication to applicant.

Form PTO-1449 INFORMATION DISCLOSURE CITATION IN AN APPLICATION <i>(Use several sheets if necessary)</i>	Docket Number 356952001300	Application Number 10/774,011
	Applicant Guanghua WU et al.	
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X	27.	10/08/96	5,563,343	Shaw et al.			
	28.	10/15/96	5,565,625	Howe et al.			
	29.	10/22/96	5,567,880	Yokota et al.			
	30.	12/24/96	5,587,601	Kurtz			
	31.	1/7/97	5,591,679	Jakobsen et al.			
	32.	1/14/97	5,594,171	Ischida et al.			
	33.	03/25/97	5,615,143	MacDonald et al.			
	34.	05/06/97	5,627,427	Das et al.			
	35.	05/13/97	5,628,917	MacDonald et al.			
	36.	06/10/97	5,637,539	Hofmann et al.			
	37.	2/17/98	5,719,073	Shaw et al.			
	38.	7/4/00	6,084,257	Petersen et al.			
X	39.	11/13/01	6,316,796	Petersen et al.			

FOREIGN PATENT DOCUMENTS

Examiner Initials	Ref. No.	Date	Document No.	Country	Class	Subclass	Translation YES NO	
X	40.	05/16/1990	EP 0 368 446	Europe				
	41.	03/23/1994	EP 0 588 371	Europe				
	42.	04/13/1994	EP 0 591 554	Europe				
	43.	07/06/1994	EP 0 605 300	Europe				
	44.	07/23/1992	DE 41 01 575	Germany			Abstract	
	45.	11/23/1995	DE 44 17 251	Germany			Abstract	
	46.	01/04/1996	DE 44 22 942	Germany			Abstract	
	47.	04/23/1979	JP 54-51490	Japan			Abstract	
	48.	08/20/1987	JP 62-190775	Japan			Abstract	
	49.	04/01/1999	WO 99/16096	WIPO				
	50.	12/08/1994	WO 94/28427	WIPO				
	51.	08/18/1994	WO 94/18697	WIPO				
X	52.	01/09/1997	WO 97/01221	WIPO				

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X	53.	02/06/1997	WO 97/04283	WIPO	—	—		
X	54.	03/14/1996	WO 96/08036	WIPO	—	—		
X	55.	03/16/2000	WO 00/14415	WIPO	—	—		

OTHER DOCUMENTS


(including author, title, Date, Pertinent Pages, Etc.)

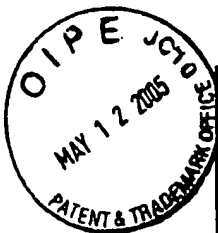
Examiner Initials	Ref. No.	Title
X	56.	Ammar, E. S. et al. (1980). "UMOS Transistors on (110) Silicon," <i>IEEE Transactions on Electron Devices</i> (ED-27)(5):907-914.
	57.	Analog Devices, Inc. (1996). "Monolithic Accelerometer With Signal Conditioning," Analog Devices ADXL50 Datasheet Specifications. pp. 1-16.
	58.	Bartha, J. W. et al. (1995). "Low Temperature Etching of Si in High Density Plasma Using SF ₆ /O ₂ ," <i>MicroElectronic Engineering</i> 27:453-456.
	59.	Bryzek, J. et al. (1994). "Micromachines on the March," <i>IEEE Spectrum</i> , pp. 20-31.
	60.	Fung, C. et al. (1985). "Deep Etching of Silicon Using Plasma", <i>Micromachining and Micropackaging of Transducers</i> pp. 159-164.
	61.	Goodenough, F. (1995). "Redesigned Surface-Micromachined Accelerometer IC Provides Increased Sensitivity of ± 1 -5 G Full Scale", <i>Electronic Design, Technology Advances</i> pp. 37 and 40 only.
	62.	Goyal, A. et al. (1993). "Formation of Silicon Reentrant Cavity Heat Sinks Using Anisotropic Etching and Direct Wafer Bonding," <i>IEEE Electron Device Letters</i> 14 (1): 29-32.
	63.	Linder, C. et al. (1991). "Deep Dry Etching Techniques as a New IC Compatible Tool for Silicon Micromachining," <i>IEEE</i> pp. 524-527.
	64.	Noworolski, J. M. et al. (1996). "Process For In-Plane And Out-Of-Plane Single-Crystal-Silicon Thermal Microactuators," <i>Sensors and Actuators</i> 55(1):65-69.
	65.	Petersen, K. (1982). "Silicon as a Mechanical Material," <i>Proceedings of the IEEE</i> 70(5):420-457.
	66.	Petersen, K. et al. (1991). "Surface Micromachined Structures Fabricated with Silicon Fusion Bonding," <i>IEEE</i> pp. 397-399.
	67.	Seidel, H. et al. (1990). "Anisotropic Etching of Crystalline Silicon in Alkaline Solutions, Orientation Dependence and Behavior of Passivation Layers," <i>J. Electrochem Soc.</i> 137(11):3612-3632.
	68.	Sherman, S. J. et al. (1992). "A Low Cost Monolithic Accelerometer; Product/Technology Update", <i>IEEE Technical Digest</i> pp. 501-504.
	69.	Suzuki, K. (1990). "Single Crystal Silicon Micro-Actuators," <i>IEEE Electronic Devices Technical Digest, International Electron Devices Meeting</i> pp. 625-628.
X	70.	Uenishi, Y. et al. (1994). "Micro-Opto-Mechanical Devices Fabricated By Anisotropic Etching of (110) Silicon," <i>Proceedings of the IEEE, Micro Electro Mechanical Systems</i> pp. 319-324.

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	71.	Yunkin, V. A, et al. (1994). "Highly Anisotropic Selective Reactive Ion Etching of Deep Trenches in Silicon", <i>Microelectronic Engineering</i> 23: 373-376.	
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ALTERNATIVE TO PTO/SB/08 a/b (06-03)

Substitute for form 1449/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Application Number	10/774,011
				Filing Date	February 6, 2004
				First Named Inventor	Guanghua WU
				Art Unit	2856
				Examiner Name	Not Yet Assigned
Sheet	1	of	1	Attorney Docket Number	356952001300

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
X	1.	US-5,016,072-A	05-14-1991	Greiff et al.	
X	2.	US-5,415,726-A	05-16-1995	Staller et al.	
X	3.	US-5,659,159-A	08-19-1997	Koopman, Jr.	
X	4.	US-5,659,195-A	08-19-1997	Kaiser et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	MM-DD-YYYY			
X	5.	WO-03/068669-A1	08-21-2003	Silex Microsystems AB		

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NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, jour nal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			T ²
	6.	European Search Report mailed on April 12, 2005 for EP patent application no. 05250525.2, 3 pages.			
	7.	Schmidt, M. A. (August 1998). "Wafer-to-Wafer Bonding for Microstructure Formation," <i>Proceedings of the IEEE</i> 86(8):1575-1585.			

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¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached.

Examiner Signature	John Chapman	Date Considered	6/26/05
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